

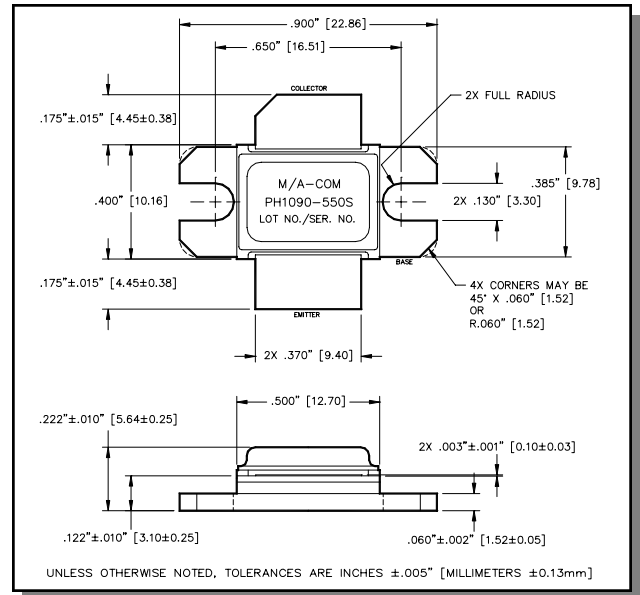
Avionics Pulsed Power Transistor
550W, 1090 MHz, 10µs Pulse, 1% Duty

M/A-COM Products
Released, 30 May 07

Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS Compliant

Outline Drawing



Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	80	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	I_C	28	A
Power Dissipation @ +25°C	P_{TOT}	3.5	kW
Storage Temperature	T_{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	$I_C = 250\text{mA}$		BV_{CES}	80	-	V
Collector-Emitter Leakage Current	$V_{CE} = 50\text{V}$		I_{CES}	-	25	mA
Thermal Resistance	$V_{CC} = 50\text{V}$, $P_{out} = 550\text{W}$	$F = 1090\text{ MHz}$	$R_{TH(JC)}$	-	0.05	°C/W
Input Power	$V_{CC} = 50\text{V}$, $P_{out} = 550\text{W}$	$F = 1090\text{ MHz}$	P_{IN}	-	100	W
Power Gain	$V_{CC} = 50\text{V}$, $P_{out} = 550\text{W}$	$F = 1090\text{ MHz}$	G_P	7.4	-	dB
Collector Efficiency	$V_{CC} = 50\text{V}$, $P_{out} = 550\text{W}$	$F = 1090\text{ MHz}$	η_C	50	-	%
Input Return Loss	$V_{CC} = 50\text{V}$, $P_{out} = 550\text{W}$	$F = 1090\text{ MHz}$	RL	-	-9	dB
Load Mismatch Tolerance	$V_{CC} = 50\text{V}$, $P_{out} = 550\text{W}$	$F = 1090\text{ MHz}$	VSWR-T	-	10:1	-
Load Mismatch Stability	$V_{CC} = 50\text{V}$, $P_{out} = 550\text{W}$	$F = 1090\text{ MHz}$	VSWR-S	-	1.5:1	-

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ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

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Typical RF Performance

Freq. (MHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (10:1)
1090	86	550	8.06	19.6	56.1	-27.7	S	P

RF Test Fixture Impedance

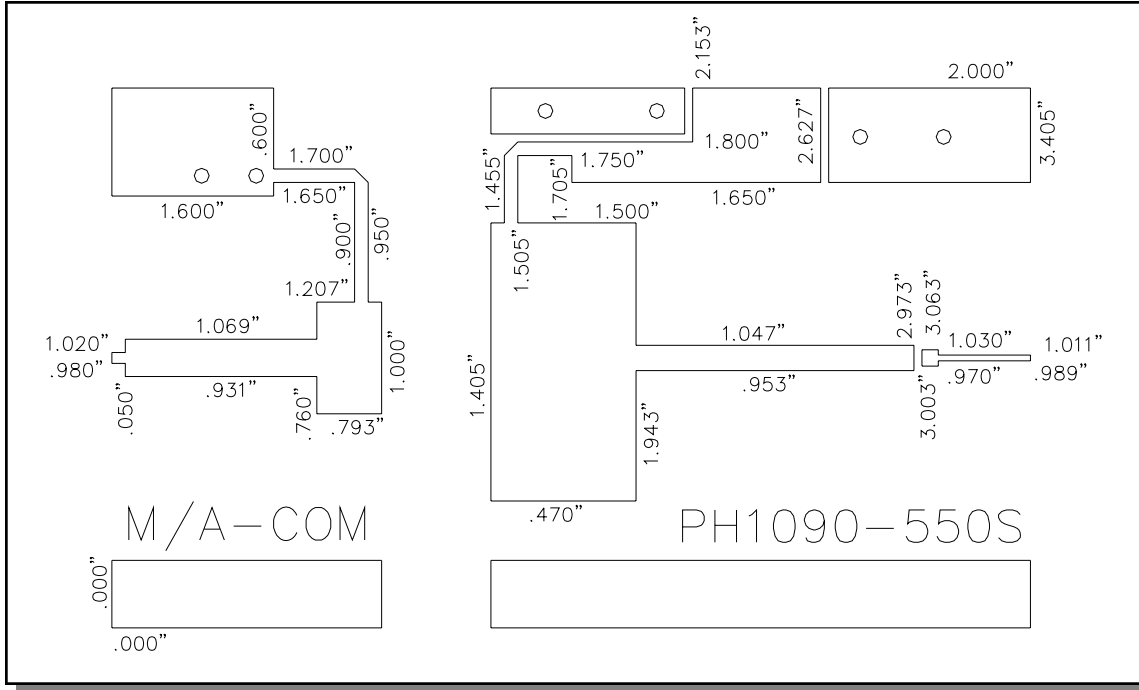
F (MHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
1030	4.0 - j3.5	1.0 - j0.9
1090	3.6 - j2.7	1.1 - j1.9



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Test Fixture Circuit Dimensions



Test Fixture Assembly

